





#### N-CHANNEL ENHANCEMENT MODE MOSFET

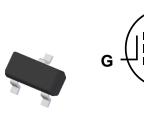
#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

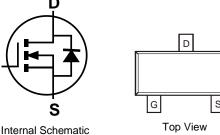
### **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (§3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

#### **SOT-23**







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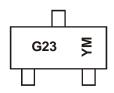
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMG2302U-7	SOT-23	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

# **Marking Information**



G23 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	2009	_	20	15	2016	2017	2018	2019	20	20	2021	2022
Code	W	_	(	0	D	E	F	G		1	ı	J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characte	eristic		Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage		V <sub>GSS</sub>	±8	V	
Continuous Drain Current (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	4.2 3.4	А	
Pulsed Drain Current (10µs Pulse, Dut	Note 6)	I <sub>DM</sub>	27	Α	

### **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		$P_{D}$	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	156	°C/W
Total Power Dissipation (Note 6)		$P_{D}$	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	91	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

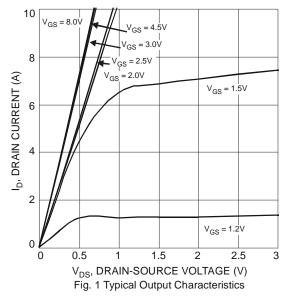
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

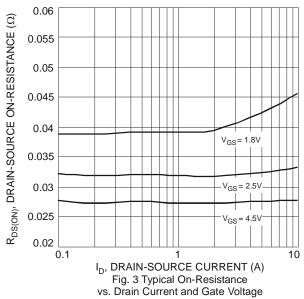
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	l	_	100	nA	$V_{DS} = 16V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	l	_	±100	nA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.4	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 50\mu A$	
Static Drain-Source On-Resistance	Passaus		_	90 120	mΩ	$V_{GS} = 4.5V, I_D = 3.6A$	
Static Drain-Source On-Nesistance	R <sub>DS(ON)</sub>	_	-			$V_{GS} = 2.5V, I_D = 3.1A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	13	_	S	$V_{DS} = 5V, I_{D} = 3.6A$	
Diode Forward Voltage	$V_{SD}$	l	0.75	1.0	V	$V_{GS} = 0V$ , $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	594.3	_	pF	101/1/	
Output Capacitance	Coss	l	64.5	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ $V_{DS} = 1.0MHz$	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	57.7	_	pF	1 = 1.0WH12	
Gate Resistance	$R_{g}$	_	1.5	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	$Q_{g}$	_	7.0	_	nC	V 45V V 40V	
Gate-Source Charge	$Q_{gs}$	_	0.9	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	$Q_{gd}$	_	1.4	_	nC	$I_D = 3.6A$	
Turn-On Delay Time	t <sub>D(on)</sub>	I	7.4	_	nS		
Turn-On Rise Time	t <sub>r</sub>	1	9.8	_	nS	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	28.1	_	nS	$R_L = 2.78\Omega$ , $R_G = 1.0\Omega$	
Turn-Off Fall Time	t <sub>f</sub>		6.7	_	nS	]	

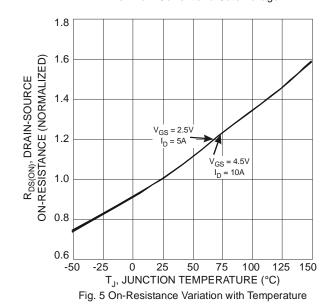
Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.









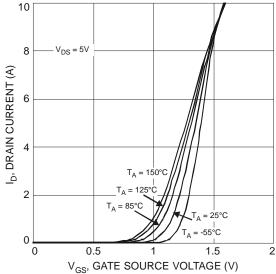


Fig. 2 Typical Transfer Characteristics

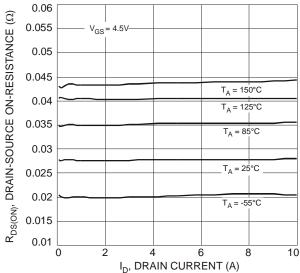


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

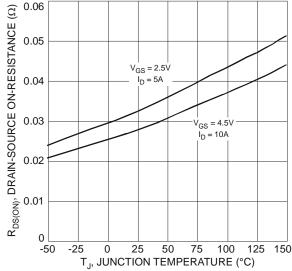


Fig. 6 On-Resistance Variation with Temperature



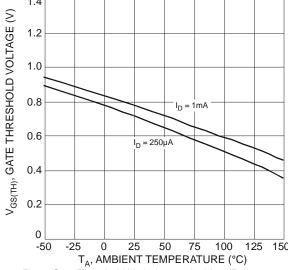
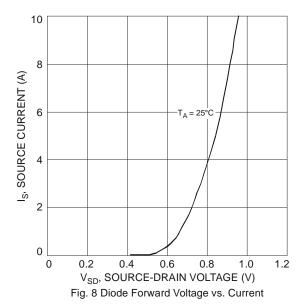
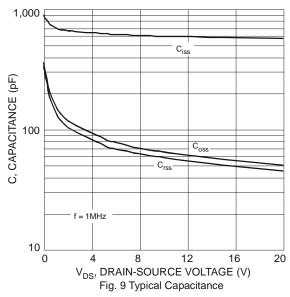
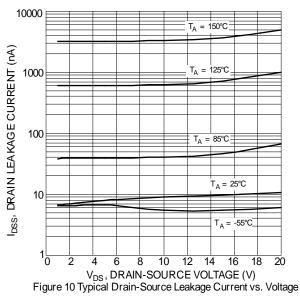


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







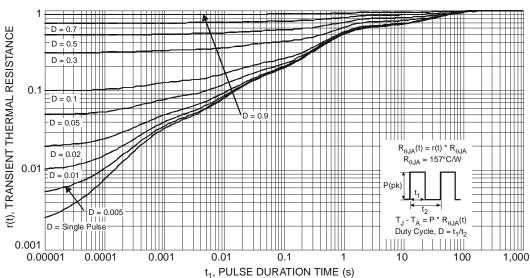


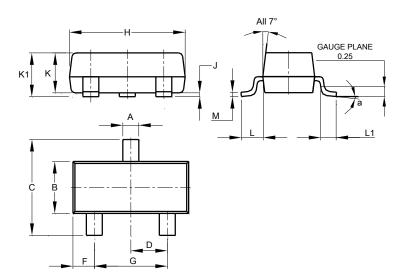
Fig. 11 Transient Thermal Response



# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### SOT-23

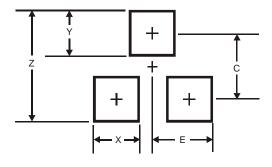


SOT-23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Η	2.80	3.00	2.90					
7	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
α	ι 8°							
All Dimensions in mm								

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT-23



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
F	1 35



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